# 2SC1360, 2SC1360A

Silicon NPN epitaxial planar type

For intermediate frequency amplification of TV image

Symbol

V<sub>CBO</sub>

V<sub>CEO</sub>

V<sub>EBO</sub>

 $I_C$ 

 $P_C$ 

Ti

T<sub>stg</sub>

Rating

50

60

45

60

4

50

1

150

-55 to +150

Unit V

v

V

mA W

°C

°C

#### Features

- High transition frequency  $f_T$
- $\bullet$  Large collector power dissipation  $P_{C}$

Parameter

Emitter-base voltage (Collector open)

Collector-base voltage (Emitter open)

Collector-emitter voltage

Collector power dissipation

(Base open)

Collector current

Junction temperature

Storage temperature

| <u>5.9±0.2</u>                           | Unit: mm                         |
|--|----------------------------------|
|  | 8.6 ±0.2                         |
| 0.7±0.1                                  | 13.510.5                         |
|  | 0.45 <sup>+02</sup>              |
| <u>0.45<sup>+0.2</sup><br/>(1.27)</u> (1 | <u>27)</u> 1: Emitter            |
|  | 2: Collector<br>3: Base          |
| 2.                                       | EIAJ: SC-51<br>TO-92L-A1 Package |

### Absolute Maximum Ratings $T_a = 25^{\circ}C$

2SC1360

2SC1360A

2SC1360

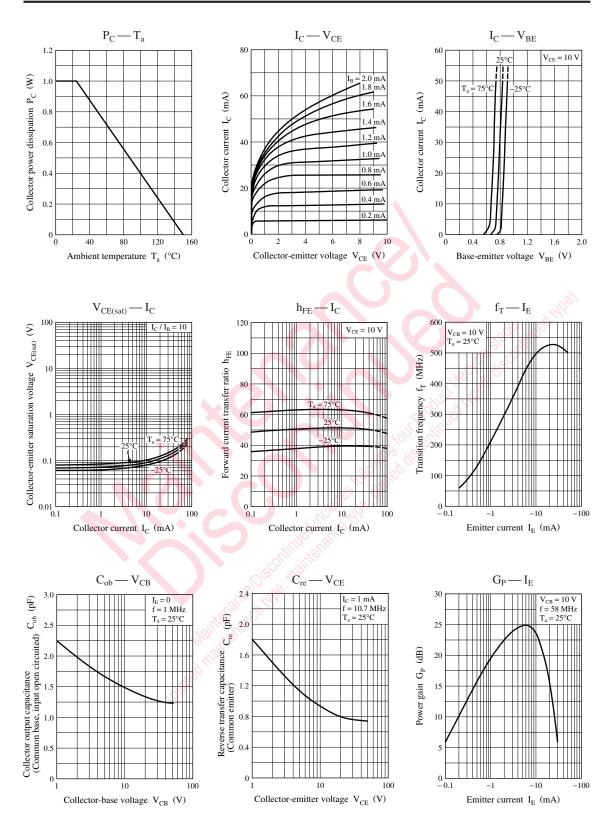
2SC1360A

## Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter                        | U            | Symbol               | Conditions   | Min | Тур  | Max | Unit |
|----------------------------------|--------------|----------------------|--|-----|------|-----|------|
| Collector-base voltage           | 2SC1360      | V <sub>CBO</sub>     | $I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$                   | 50  |      |     | V    |
| (Emitter open)                   | 2SC1360A     |                      | in the state   | 60  |      |     |      |
| Collector-emitter voltage        | 2SC1360      | V <sub>CEO</sub>     | $I_{\rm C} = 3 \text{ mA}, I_{\rm B} = 0$                          | 45  |      |     | V    |
| (Base open)                      | 2SC1360A     |                      | $I_C = 1 \text{ mA}, I_B = 0$                                      | 60  |      |     |      |
| Emitter-base voltage (Colle      | ctor open)   | V <sub>EBO</sub>     | $I_{\rm E} = 100 \ \mu A, \ I_{\rm C} = 0$                         | 4   |      |     | V    |
| Collector-base cutoff current (E | mitter open) | I <sub>CBO</sub>     | $V_{CB} = 20 V, I_E = 0$   |     |      | 100 | nA   |
| Forward current transfer rat     | io 👋         | h <sub>FE</sub>      | $V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$                     | 20  | 50   | 100 | _    |
| Collector-emitter saturation     | voltage      | V <sub>CE(sat)</sub> | $I_{C} = 20 \text{ mA}, I_{B} = 2 \text{ mA}$                      |     |      | 0.4 | V    |
| Transition frequency             | 2SC1360      | f <sub>T</sub>       | $V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 100 \text{ MHz}$ | 300 | 500  |     | MHz  |
|                                  | 2SC1360A     |                      |  | 300 |      |     |      |
| Reverse transfer capacitance     | 2SC1360      | C <sub>re</sub>      | $V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$ |     | 0.96 | 1.5 | pF   |
| (Common emitter)                 | 2SC1360A     |                      |  |     |      | 1.5 |      |
| Power gain                       | 2SC1360      | G <sub>P</sub>       | $V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 58 \text{ MHz}$  | 22  | 26   | 30  | dB   |
|                                  | 2SC1360A     | ]                    |  | 22  |      | 30  |      |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## Panasonic



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